## PATENT ABSTRACTS OF JAPAN

(11)Publication number:

63-077050

(43) Date of publication of application: 07.04.1988

(51)Int.Cl.

G03C G03F 7/00

H01L 21/30

(21)Application number : **61-222718** 

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(22) Date of filing:

20.09.1986

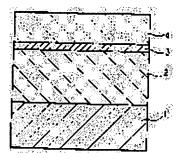
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## (54) INTERLAYER MATERIAL FOR THREE-LAYER RESIST AND PATTERN FORMING **METHOD**

(57) Abstract:

PURPOSE: To form an upper layer resist film uniform in film thickness by forming an interlayer composed essentially of specified organopolysiloxane and incorporating an organic peroxide as a cross-linking agent to form a 3-layer resist. CONSTITUTION: The interlayer of the 3-layer resist is composed essentially of organopolysiloxane represented by the formula shown on the right in which each of R is optionally same or different, and each is H, OH, alkoxy, or a hydrocarbon group; m+n+p+q=1, m>0, n, p,  $q\geq0$ ,  $m/q\leq1$ (q>0),  $m/p \le 0.3$  (p>0), and p and q are simultaneously not 0. Further, the cross-linking agent containing the organic peroxide is incorporated in the interlayer. A substrate pattern is formed by using the 3-layer resist as follows: Spin coating the semiconductor substrate 1 with a lower layer resist 2 made of an organic polymer, then heat treating it, spin coating the lower layer 2 with the interlayer material 3 composed of the organopolysiloxane containing a prescribed amount of organic peroxide, heat treating it, spin coating the interlayer 3 with an upper layer resist 4 made of a polymer to be cross-linked or

(R.Sid. Cara) and (Bisto) (Bisto) (Bisto) (((0,)) で式作、RIC、同一をしくは異っていても2 ショウらなる日から選択れる一位であり、 m + n + p + q = 1 . c > 0 . n . p . c



decomposed by radiation, and finally heat treating it, thus permitting the good upper layer resist 4 uniform in thickness to be formed by using this interlayer.